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L	Hits	Search Text	DB	Time stamp
Number 1	2181	(TEOS or "tetra ethyl ortho silicate")	USPAT;	2003/07/22
1	2101	and (implanted or implanting or	EPO; JPO;	14:26
1	l .	implantation) and (boron or phosphorus)	IBM TDB	
	'	and (HF or vapor or hydrofluoric) and	12	
		(contact or opening or trenches)		
2	1702	(TEOS or "tetra ethyl ortho silicate")	USPAT;	2003/07/22
-		and (implanted or implanting or	EPO; JPO;	14:27
		implantation) and (boron or phosphorus)	IBM TDB	
		and (HF or vapor or hydrofluoric) and	l - · .	
		(contact or opening or trenches) and		
		(resist or photoresist)		
4	35	(TEOS or "tetra ethyl ortho silicate")	USPAT;	2003/07/22
		same (implanted or implanting or	EPO; JPO;	14:31
•		implantation) same (boron or phosphorus)	IBM_TDB	
		same (HF or vapor or hydrofluoric) same		
,		(contact or opening or trenches) and		
-	1700	(resist or photoresist)	IICDAM.	2002/07/22
5	1702	(TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or	USPAT; EPO; JPO;	2003/07/22
	,	and (implanted or implanting or implantation) and (boron or phosphorus)	IBM TDB	13.03
		and (HF or vapor or hydrofluoric) and	100-100	.
		(contact or opening or trenches) and		·
		(resist or photoresist)		
6	2065	dual adj damascene	USPAT;	2003/07/22
1			EPO; JPO;	14:34
			IBM TDB	
7	39	((TEOS or "tetra ethyl ortho silicate")	USPAT;	2003/07/22
		and (implanted or implanting or	EPO; JPO;	14:34
		implantation) and (boron or phosphorus)	IBM_TDB	
Ì		and (HF or vapor or hydrofluoric) and		
		(contact or opening or trenches) and		
		(resist or photoresist)) and (dual adj		
		damascene)	*******	2002/07/20
8	1		USPAT	2003/07/22
9	1642	(TEOS or "tetra ethyl ortho silicate")	USPAT;	14:38
3	1042	and (implanted or implanting or	EPO; JPO;	16:03
	-	implantation) and (boron or phosphorus)	IBM TDB	10.03
		and (HF or vapor or hydrofluoric) and	15155	
		(contact or opening or trenches) and		
		(· · · · · · · · · · · · · · · · · · ·	1	
1		(resist or photoresist) and etch\$3 and		
1 1 0		<pre>(resist or photoresist) and etch\$3 and semiconductor</pre>		
10	1184	- · · · · · · · · · · · · · · · · · · ·	USPAT;	2003/07/22
10	. 1184	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or	USPAT; EPO; JPO;	2003/07/22 15:05
10	1184	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus)		1 1
10	1184	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and	EPO; JPO;	1 1
10	. 1184	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and	EPO; JPO;	1 1
	. 1184	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and	EPO; JPO;	1 1
		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls.	EPO; JPO; IBM_TDB	15:05
10		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate")	EPO; JPO; IBM_TDB USPAT;	15:05 2003/07/22
		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or	EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22
		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus)	EPO; JPO; IBM_TDB USPAT;	15:05 2003/07/22
		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or	EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22
		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or	EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22
		semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or	EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22
11	856	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor	USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09
11	856	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate")	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22
11	856	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22 15:09 2003/07/22
11	856	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22 15:09 2003/07/22
11	856	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO;	15:05 2003/07/22 15:09 2003/07/22
11	856 65	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening)	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22 15:34
11	856	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening) (TEOS or "tetra ethyl ortho silicate")	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22 15:34
11	856 65	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening) (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or	EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22 15:34
11	856 65	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening) (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus)	USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22 15:34
11	856 65	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (Second adj opening) (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or	EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22 15:34
11	856 65	semiconductor ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening) (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus)	EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB USPAT; EPO; JPO; IBM_TDB	15:05 2003/07/22 15:09 2003/07/22 15:34





14	948	(stacked or stack or stacking) same	USPAT;	2003/07/22
		implant\$3 same (opening or contact or	EPO; JPO;	16:02
		trenches)	IBM_TDB	
15	280	((stacked or stack or stacking) same	USPAT;	2003/07/22
		implant\$3 same (opening or contact or	EPO; JPO;	16:03
· .		trenches)) and (boron or phosphorus) and	IBM_TDB	
		(HF or vapor)		